

Huili Grace Xing

List of Publications by Year in descending order

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337
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#	ARTICLE	IF	CITATIONS
1	Epitaxial Ferrimagnetic Mn ₄ N Thin Films on GaN by Molecular Beam Epitaxy. IEEE Transactions on Magnetics, 2022, 58, 1-6.	1.2	3
2	In-situ Crystalline AlN Passivation for Reduced RF Dispersion in Strained Channel AlN/GaN/AlN High-Electron-Mobility Transistors. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, 2100452.	0.8	9
3	Nucleation, growth, and stability of WSe ₂ thin films deposited on HOPG examined using in situ, real-time synchrotron x-ray radiation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Plasma, 2022, 40, 012103.	0.9	1
4	Infrared dielectric functions and Brillouin zone center phonons of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ compared to AlN and GaN . Physical Review Materials, 2022, 6, 014401.	0.9	10
5	Very High Density (>10 ¹⁴ cm ⁻²) Polarization-Induced 2D Hole Gases Observed in Undoped Pseudomorphic InGaN/AlN Heterostructures. Advanced Electronic Materials, 2022, 8, .	2.6	6
6	Breakdown Mechanisms in $\text{In}^2\text{-Ga}_{23}\text{O}_3$ Trench-MOS Schottky-Barrier Diodes. IEEE Transactions on Electron Devices, 2022, 69, 75-81.	1.6	9
7	Quantitative scanning microwave microscopy of 2D electron and hole gases in AlN/GaN heterostructures. Applied Physics Letters, 2022, 120, 012103.	1.5	2
8	A unified thermionic and thermionic-field emission (TE-TFE) model for ideal Schottky reverse-bias leakage current. Journal of Applied Physics, 2022, 131, .	1.1	11
9	High thermal conductivity and ultrahigh thermal boundary conductance of homoepitaxial AlN thin films. APL Materials, 2022, 10, .	2.2	12
10	Distributed polarization-doped GaN pn diodes with near-unity ideality factor and avalanche breakdown voltage of 1.25 kV. Applied Physics Letters, 2022, 120, .	1.5	3
11	Extending the Kinetic and Thermodynamic Limits of Molecular-Beam Epitaxy Utilizing Suboxide Sources or Metal-Oxide-Catalyzed Epitaxy. Physical Review Applied, 2022, 17, .	1.5	11
12	Infrared-active phonon modes and static dielectric constants in $\text{Al}_{1-x}\text{Ga}_x\text{N}$ (0.18 ≤ x ≤ 0.54) alloys. Applied Physics Letters, 2022, 120, .	1.5	4
13	Optically pumped deep-UV multimode lasing in AlGaIn double heterostructure grown by molecular beam homoepitaxy. AIP Advances, 2022, 12, .	0.6	7
14	Epitaxial ScAlInN on GaN exhibits attractive high-K dielectric properties. Applied Physics Letters, 2022, 120, .	1.5	17
15	N-polar GaN p-n junction diodes with low ideality factors. Applied Physics Express, 2022, 15, 064004.	1.1	4
16	Structural and electronic properties of NbN/GaN junctions grown by molecular beam epitaxy. APL Materials, 2022, 10, 051103.	2.2	3
17	AlN quasi-vertical Schottky barrier diode on AlN bulk substrate using Al _{0.9} Ga _{0.1} N current spreading layer. Applied Physics Express, 2022, 15, 061007.	1.1	7
18	X-band epi-BAW resonators. Journal of Applied Physics, 2022, 132, .	1.1	8

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19	First RF Power Operation of AlN/GaN/AlN HEMTs With >3 A/mm and 3 W/mm at 10 GHz. IEEE Journal of the Electron Devices Society, 2021, 9, 121-124.	1.2	33
20	Crystal orientation dictated epitaxy of ultrawide-bandgap 5.4- to 8.6-eV $\hat{\pm}$ -(AlGa) $\langle\text{sub}\rangle 2\langle\text{sub}\rangle$ O $\langle\text{sub}\rangle 3\langle\text{sub}\rangle$ on m-plane sapphire. Science Advances, 2021, 7, .	4.7	71
21	Advanced concepts in Ga ₂ O ₃ power and RF devices. Semiconductors and Semimetals, 2021, 107, 23-47.	0.4	3
22	An all-epitaxial nitride heterostructure with concurrent quantum Hall effect and superconductivity. Science Advances, 2021, 7, .	4.7	12
23	Electric Fields and Surface Fermi Level in Undoped GaN/AlN Two-â€Dimensional Hole Gas Heterostructures. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2000573.	1.2	5
24	Anisotropic dielectric functions, band-to-band transitions, and critical points in $\langle b \rangle \langle i \rangle \hat{\pm} \langle /i \rangle \langle /b \rangle$ -Ga ₂ O ₃ . Applied Physics Letters, 2021, 118, .	1.5	19
25	Unexplored MBE growth mode reveals new properties of superconducting NbN. Physical Review Materials, 2021, 5, .	0.9	10
26	Molecular beam epitaxy of polar III-nitride resonant tunneling diodes. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, 023409.	0.9	4
27	Adsorption-controlled growth of Ga ₂ O ₃ by suboxide molecular-beam epitaxy. APL Materials, 2021, 9, .	2.2	38
28	MBE growth and donor doping of coherent ultrawide bandgap AlGaN alloy layers on single-crystal AlN substrates. Applied Physics Letters, 2021, 118, .	1.5	16
29	Enhanced efficiency in bottom tunnel junction InGaN blue LEDs. , 2021, , .		6
30	Next generation electronics on the ultrawide-bandgap aluminum nitride platform. Semiconductor Science and Technology, 2021, 36, 044001.	1.0	42
31	Ultrafast dynamics of gallium vacancy charge states in $\langle\text{mml}:\text{math}\text{xmlns:mml}=\text{"http://www.w3.org/1998/Math/MathML"}\rangle\langle\text{mml}:\text{mrow}\rangle\langle\text{mml}:\text{mi}\rangle\hat{2}\langle\text{mml}:\text{mi}\rangle\langle\text{mml}:\text{mtext}\rangle\hat{\text{''}}\langle\text{mml}:\text{mtext}\rangle\langle\text{mml}:\text{msub}\text{mathvariant}=\text{"normal"}\rangle\text{O}\langle\text{mml}:\text{mi}\rangle\langle\text{mml}:\text{mn}\rangle 3\langle\text{mml}:\text{mn}\rangle\langle\text{mml}:\text{msub}\rangle\langle\text{mml}:\text{mrow}\rangle\langle\text{mml}:\text{math}\rangle$. Physical Review Research, 2021, 3, .	1.3	6
32	$\langle i \rangle \hat{3} \langle /i \rangle$ -phase inclusions as common structural defects in alloyed $\langle i \rangle \hat{2} \langle /i \rangle$ -(Al $\langle i \rangle x \langle /i \rangle$ Ga $1\hat{\text{''}} \langle i \rangle x \langle /i \rangle$) ₂ O ₃ and doped $\langle i \rangle \hat{2} \langle /i \rangle$ -Ga ₂ O ₃ films. APL Materials, 2021, 9, .	2.2	23
33	ON-Resistance of Ga $\langle\text{sub}\rangle 2\langle\text{sub}\rangle$ O $\langle\text{sub}\rangle 3\langle\text{sub}\rangle$ Trench-MOS Schottky Barrier Diodes: Role of Sidewall Interface Trapping. IEEE Transactions on Electron Devices, 2021, 68, 2420-2426.	1.6	19
34	Temperature-dependent Lowering of Coercive Field in 300 nm Sputtered Ferroelectric Al $\langle\text{sub}\rangle 0.70\langle\text{sub}\rangle$ Sc $\langle\text{sub}\rangle 0.30\langle\text{sub}\rangle$ N. , 2021, , .		10
35	Large Signal Response of AlN/GaN/AlN HEMTs at 30 GHz. , 2021, , .		5
36	High-conductivity polarization-induced 2D hole gases in undoped GaN/AlN heterojunctions enabled by impurity blocking layers. Journal of Applied Physics, 2021, 130, 025703.	1.1	12

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37	Thermal stability of epitaxial $\text{In}_{\pm}\text{-Ga}_2\text{O}_3$ and $(\text{Al,Ga})_2\text{O}_3$ layers on m-plane sapphire. Applied Physics Letters, 2021, 119, .	1.5	30
38	High-frequency and below bandgap anisotropic dielectric constants in $\text{In}_{\pm}\text{-}(\text{Al}_{\text{x}}\text{Ga}_{1-\text{x}})_2\text{O}_3$ ($0 \leq x \leq 1$). Applied Physics Letters, 2021, 119, .	1.5	14
39	Dislocation and indium droplet related emission inhomogeneities in InGaN LEDs. Journal Physics D: Applied Physics, 2021, 54, 495106.	1.3	6
40	Thermal design of multi-fin Ga_2O_3 vertical transistors. Applied Physics Letters, 2021, 119, .	1.5	17
41	Strong effect of scandium source purity on chemical and electronic properties of epitaxial $\text{Sc}_x\text{Al}_{1-x}\text{N}/\text{GaN}$ heterostructures. APL Materials, 2021, 9, .	2.2	14
42	Polarization-induced 2D hole gases in pseudomorphic undoped GaN/AlN heterostructures on single-crystal AlN substrates. Applied Physics Letters, 2021, 119, .	1.5	15
43	SiC Substrate-Integrated Waveguides for High-Power Monolithic Integrated Circuits Above 110 GHz. , 2021, , .		9
44	Momentum-resolved electronic structure and band offsets in an epitaxial NbN/GaN superconductor/semiconductor heterojunction. Science Advances, 2021, 7, eabi5833.	4.7	5
45	Degradation Mechanisms of GaN-Based Vertical Devices: A Review. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900750.	0.8	8
46	Oxygen Incorporation in the Molecular Beam Epitaxy Growth of $\text{Sc}_x\text{Ga}_{1-x}\text{N}$ and $\text{Sc}_x\text{Al}_{1-x}\text{N}$. Physica Status Solidi (B): Basic Research, 2020, 257, 1900612.	0.7	29
47	Molecular Beam Epitaxy Growth of Large-Area GaN/AlN 2D Hole Gas Heterostructures. Physica Status Solidi (B): Basic Research, 2020, 257, 1900567.	0.7	12
48	Nitride LEDs and Lasers with Buried Tunnel Junctions. ECS Journal of Solid State Science and Technology, 2020, 9, 015018.	0.9	12
49	Field-Plated Ga_2O_3 Trench Schottky Barrier Diodes With a BV^2 of up to 0.95 GW/cm^2 . IEEE Electron Device Letters, 2020, 41, 107-110.	2.2	184
50	Molecular Beam Epitaxy of Transition Metal Nitrides for Superconducting Device Applications. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900675.	0.8	16
51	Epitaxial niobium nitride superconducting nanowire single-photon detectors. Applied Physics Letters, 2020, 117, .	1.5	25
52	N-polar GaN/AlN resonant tunneling diodes. Applied Physics Letters, 2020, 117, .	1.5	12
53	Guiding Principles for Trench Schottky Barrier Diodes Based on Ultrawide Bandgap Semiconductors: A Case Study in Ga_2O_3 . IEEE Transactions on Electron Devices, 2020, 67, 3938-3947.	1.6	36
54	Thermionic emission or tunneling? The universal transition electric field for ideal Schottky reverse leakage current: A case study in $\text{In}_{\pm}\text{-Ga}_2\text{O}_3$. Applied Physics Letters, 2020, 117, .	1.5	24

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55	Prospects for Wide Bandgap and Ultrawide Bandgap CMOS Devices. IEEE Transactions on Electron Devices, 2020, 67, 4010-4020.	1.6	73
56	Bottom tunnel junction blue light-emitting field-effect transistors. Applied Physics Letters, 2020, 117, 031107.	1.5	5
57	Very High Parallel-Plane Surface Electric Field of 4.3 MV/cm in Ga ₂ O ₃ Schottky Barrier Diodes with PtO _x Contacts. , 2020, , .		8
58	Light-emitting diodes with AlN polarization-induced buried tunnel junctions: A second look. Applied Physics Letters, 2020, 117, .	1.5	11
59	Structural and piezoelectric properties of ultra-thin ScxAl1-xN films grown on GaN by molecular beam epitaxy. Applied Physics Letters, 2020, 117, .	1.5	34
60	Trapping and Detrapping Mechanisms in \hat{I}^2 -Ga ₂ O ₃ Vertical FinFETs Investigated by Electro-Optical Measurements. IEEE Transactions on Electron Devices, 2020, 67, 3954-3959.	1.6	24
61	Intra- and inter-conduction band optical absorption processes in \hat{I}^2 -Ga ₂ O ₃ . Applied Physics Letters, 2020, 117, 072103.	1.5	10
62	Molecular beam homoepitaxy on bulk AlN enabled by aluminum-assisted surface cleaning. Applied Physics Letters, 2020, 116, .	1.5	26
63	Near-ideal reverse leakage current and practical maximum electric field in \hat{I}^2 -Ga ₂ O ₃ Schottky barrier diodes. Applied Physics Letters, 2020, 116, .	1.5	86
64	Spin-orbit torque field-effect transistor (SOTFET): Proposal for a magnetoelectric memory. Applied Physics Letters, 2020, 116, 242405.	1.5	9
65	Impact of Residual Carbon on Avalanche Voltage and Stability of Polarization-Induced Vertical GaN p-n Junction. IEEE Transactions on Electron Devices, 2020, 67, 3978-3982.	1.6	4
66	Fighting Broken Symmetry with Doping: Toward Polar Resonant Tunneling Diodes with Symmetric Characteristics. Physical Review Applied, 2020, 13, .	1.5	11
67	GaN HEMTs on Si With Regrown Contacts and Cutoff/Maximum Oscillation Frequencies of 250/204 GHz. IEEE Electron Device Letters, 2020, 41, 689-692.	2.2	69
68	AlN Epitaxial Bulk Acoustic Wave Resonators. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900786.	0.8	10
69	Multiferroic LuFeO ₃ on GaN by molecular-beam epitaxy. Applied Physics Letters, 2020, 116, .	1.5	8
70	Surface control and MBE growth diagram for homoepitaxy on single-crystal AlN substrates. Applied Physics Letters, 2020, 116, .	1.5	26
71	Magnetic properties of MBE grown Mn ₄ N on MgO, SiC, GaN and Al ₂ O ₃ substrates. AIP Advances, 2020, 10, .	0.6	6
72	Gallium nitride tunneling field-effect transistors exploiting polarization fields. Applied Physics Letters, 2020, 116, .	1.5	7

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73	Fully transparent field-effect transistor with high drain current and on-off ratio. APL Materials, 2020, 8, .	2.2	23
74	Layered two-dimensional selenides and tellurides grown by molecular beam epitaxy. , 2020, , 235-269.		1
75	Resonant Tunneling Transport in Polar III-Nitride Heterostructures. , 2020, , 215-247.		2
76	GaN/AlN p-channel HFETs with $I_{\text{max}} > 420$ mA/mm and ~ 20 GHz f_{T} / f_{MAX} . , 2020, , .		13
77	Monolithically p-down nitride laser diodes and LEDs obtained by MBE using buried tunnel junction design. , 2020, , .		2
78	Enhanced injection efficiency and light output in bottom tunnel-junction light-emitting diodes. Optics Express, 2020, 28, 4489.	1.7	19
79	GaN/AlGaIn 2DEGs in the quantum regime: Magneto-transport and photoluminescence to 60 tesla. Applied Physics Letters, 2020, 117, 262105.	1.5	1
80	Field-Effect Transistors 5. Springer Series in Materials Science, 2020, , 639-660.	0.4	0
81	High Internal Quantum Efficiency from AlGaIn-delta-GaN Quantum Well at 260 nm. , 2020, , .		3
82	Distributed-feedback blue laser diode utilizing a tunnel junction grown by plasma-assisted molecular beam epitaxy. Optics Express, 2020, 28, 35321.	1.7	9
83	Self-assembly and properties of domain walls in BiFeO3 layers grown via molecular-beam epitaxy. APL Materials, 2019, 7, .	2.2	7
84	1.6 kV Vertical Ga ₂ O ₃ FinFETs With Source-Connected Field Plates and Normally-off Operation. , 2019, , .		31
85	Band Structure Engineering of Layered WSe ₂ <i>via</i> One-Step Chemical Functionalization. ACS Nano, 2019, 13, 7545-7555.	7.3	21
86	High Breakdown Voltage in RF AlN/GaN/AlN Quantum Well HEMTs. IEEE Electron Device Letters, 2019, 40, 1293-1296.	2.2	79
87	Molecular beam epitaxial growth of scandium nitride on hexagonal SiC, GaN, and AlN. Applied Physics Letters, 2019, 115, .	1.5	24
88	Breakdown Walkout in Polarization-Doped Vertical GaN Diodes. IEEE Transactions on Electron Devices, 2019, 66, 4597-4603.	1.6	9
89	Room-Temperature Graphene-Nanoribbon Tunneling Field-Effect Transistors. Npj 2D Materials and Applications, 2019, 3, .	3.9	26
90	High-mobility two-dimensional electron gases at AlGaIn/GaN heterostructures grown on GaN bulk wafers and GaN template substrates. Applied Physics Express, 2019, 12, 121003.	1.1	9

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91	Significantly reduced thermal conductivity in $\text{Al}_{0.1}\text{Ga}_{0.9}\text{O}_3/\text{Ga}_2\text{O}_3$ superlattices. Applied Physics Letters, 2019, 115, .	1.5	22
92	Magnetotransport and superconductivity in InBi films grown on Si(111) by molecular beam epitaxy. Journal of Applied Physics, 2019, 126, 103901.	1.1	4
93	A polarization-induced 2D hole gas in undoped gallium nitride quantum wells. Science, 2019, 365, 1454-1457.	6.0	106
94	Wurtzite phonons and the mobility of a GaN/AlN 2D hole gas. Applied Physics Letters, 2019, 114, .	1.5	19
95	Polarization control in nitride quantum well light emitters enabled by bottom tunnel-junctions. Journal of Applied Physics, 2019, 125, 203104.	1.1	24
96	Realization of GaN PolarMOS using selective-area regrowth by MBE and its breakdown mechanisms. Japanese Journal of Applied Physics, 2019, 58, SCCD15.	0.8	18
97	The new nitrides: layered, ferroelectric, magnetic, metallic and superconducting nitrides to boost the GaN photonics and electronics eco-system. Japanese Journal of Applied Physics, 2019, 58, SC0801.	0.8	69
98	Fiber Reinforced Layered Dielectric Nanocomposite. Advanced Functional Materials, 2019, 29, 1900056.	7.8	64
99	Blue (In,Ga)N light-emitting diodes with buried $\text{p}^+\text{n}^+\text{p}^+$ tunnel junctions by plasma-assisted molecular beam epitaxy. Japanese Journal of Applied Physics, 2019, 58, 060914.	0.8	6
100	Fin-channel orientation dependence of forward conduction in kV-class Ga_2O_3 trench Schottky barrier diodes. Applied Physics Express, 2019, 12, 061007.	1.1	50
101	Bandgap narrowing and Mott transition in Si-doped $\text{Al}_{0.7}\text{Ga}_{0.3}\text{N}$. Applied Physics Letters, 2019, 114, .	1.5	13
102	Electronic structure of SnSe ₂ films grown by molecular beam epitaxy. Applied Physics Letters, 2019, 114, 091602.	1.5	12
103	Broken Symmetry Effects due to Polarization on Resonant Tunneling Transport in Double-Barrier Nitride Heterostructures. Physical Review Applied, 2019, 11, .	1.5	25
104	Materials Relevant to Realizing a Field-Effect Transistor Based on Spin-Orbit Torques. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2019, 5, 158-165.	1.1	1
105	Single and multi-fin normally-off Ga_2O_3 vertical transistors with a breakdown voltage over 2.6 kV. , 2019, , .		50
106	GaN/AlN Schottky-gate p-channel HFETs with InGaN contacts and 100 mA/mm on-current. , 2019, , .		22
107	Thermal conductivity of crystalline AlN and the influence of atomic-scale defects. Journal of Applied Physics, 2019, 126, .	1.1	75
108	Modeling and Circuit Design of Associative Memories With Spin-Orbit Torque FETs. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2019, 5, 197-205.	1.1	6

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109	Rotationally aligned hexagonal boron nitride on sapphire by high-temperature molecular beam epitaxy. <i>Physical Review Materials</i> , 2019, 3, .	0.9	25
110	GaN/NbN epitaxial semiconductor/superconductor heterostructures. <i>Nature</i> , 2018, 555, 183-189.	13.7	116
111	Steep Sub-Boltzmann Switching in AlGaN/GaN Phase-FETs With ALD VO ₂ . <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 945-949.	1.6	13
112	Band offset and electron affinity of MBE-grown SnSe ₂ . <i>Applied Physics Letters</i> , 2018, 112, .	1.5	13
113	234-nm and 246-nm AlN-Delta-GaN quantum well deep ultraviolet light-emitting diodes. <i>Applied Physics Letters</i> , 2018, 112, .	1.5	55
114	Development of GaN Vertical Trench-MOSFET With MBE Regrown Channel. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 2558-2564.	1.6	46
115	Enhancement-Mode Ga ₂ O ₃ Vertical Transistors With Breakdown Voltage >1 kV. <i>IEEE Electron Device Letters</i> , 2018, 39, 869-872.	2.2	241
116	Room temperature microwave oscillations in GaN/AlN resonant tunneling diodes with peak current densities up to 220 kA/cm ² . <i>Applied Physics Letters</i> , 2018, 112, .	1.5	51
117	MBE growth of few-layer 2H-MoTe ₂ on 3D substrates. <i>Journal of Crystal Growth</i> , 2018, 482, 61-69.	0.7	43
118	2.44 kV Ga ₂ O ₃ /AlN vertical trench Schottky barrier diodes with very low reverse leakage current. , 2018, , .		39
119	1230-V AlN-GaN trench Schottky barrier diodes with an ultra-low leakage current of 10^{-4} A/cm ² . <i>Applied Physics Letters</i> , 2018, 113, .	1.5	94
120	Measurement of ultrafast dynamics of photoexcited carriers in AlN-GaN by two-color optical pump-probe spectroscopy. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	19
121	Gate-Recessed E-mode p-Channel HFET With High On-Current Based on GaN/AlN 2D Hole Gas. <i>IEEE Electron Device Letters</i> , 2018, 39, 1848-1851.	2.2	62
122	Comparison of unit cell coupling for grating-gate and high electron mobility transistor array THz resonant absorbers. <i>Journal of Applied Physics</i> , 2018, 124, .	1.1	6
123	Breakdown mechanism in 1 kA/cm ² and 960 V E-mode AlN-GaN vertical transistors. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	128
124	1.5 kV Vertical Ga ₂ O ₃ Trench-MIS Schottky Barrier Diodes. , 2018, , .		16
125	Enhancement of punch-through voltage in GaN with buried p-type layer utilizing polarization-induced doping. , 2018, , .		2
126	Challenges and Opportunities in Molecular Beam Epitaxy Growth of 2D Crystals. , 2018, , 443-485.		5

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127	Activation of buried p-GaN in MOCVD-regrown vertical structures. Applied Physics Letters, 2018, 113, 062105.	1.5	35
128	Demonstration of AlGaIn-delta-GaN QW by plasma-assisted molecular beam epitaxy for 260-nm ultraviolet light emitting diodes. , 2018, , .		1
129	Design and Realization of GaN Trench Junction-Barrier-Schottky-Diodes. IEEE Transactions on Electron Devices, 2017, 64, 1635-1641.	1.6	76
130	Inductively-coupled-plasma reactive ion etching of single-crystal $\text{In}^{2-}\text{Ga}_{2-}\text{O}_{3-}$. Japanese Journal of Applied Physics, 2017, 56, 030304.	0.8	46
131	Physics and polarization characteristics of 298-nm AlN-delta-GaN quantum well ultraviolet light-emitting diodes. Applied Physics Letters, 2017, 110, .	1.5	44
132	Strained GaN quantum-well FETs on single crystal bulk AlN substrates. Applied Physics Letters, 2017, 110, .	1.5	48
133	MBE-grown 232-270-nm deep-UV LEDs using monolayer thin binary GaN/AlN quantum heterostructures. Applied Physics Letters, 2017, 110, .	1.5	105
134	Single-crystal N-polar GaN p-n diodes by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2017, 110, .	1.5	14
135	Electron mobility in polarization-doped Al _{0.2} GaN with a low concentration near 10^{17} cm^{-3} . Applied Physics Letters, 2017, 110, 182102.	1.5	11
136	Electronic Structure of the Metastable Epitaxial Rock-Salt SnSe $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:mo stretchy="false"} \rangle \{ \langle \text{mml:mo} \rangle \langle \text{mml:mn} \rangle 111 \langle \text{mml:mn} \rangle \langle \text{mml:mo} \rangle \text{stretchy="false"} \} \langle \text{mml:mo} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:math} \rangle$ Topological Crystalline Insulator. Physical Review X, 2017, 7, .	2.8	17
137	New Tunneling Features in Polar III-Nitride Resonant Tunneling Diodes. Physical Review X, 2017, 7, .	2.8	42
138	Terahertz spectroscopy of an electron-hole bilayer system in AlN/GaN/AlN quantum wells. Applied Physics Letters, 2017, 111, .	1.5	9
139	Deep-UV emission at 219-nm from ultrathin MBE GaN/AlN quantum heterostructures. Applied Physics Letters, 2017, 111, .	1.5	54
140	GaN vertical nanowire and fin power MISFETs. , 2017, , .		8
141	Selective Chemical Response of Transition Metal Dichalcogenides and Metal Dichalcogenides in Ambient Conditions. ACS Applied Materials & Interfaces, 2017, 9, 29255-29264.	4.0	24
142	600 V GaN vertical V-trench MOSFET with MBE regrown channel. , 2017, , .		14
143	Tunneling devices over van der Waals bonded hetero-interface. , 2017, , .		0
144	1.1-kV Vertical GaN p-n Diodes With p-GaN Regrown by Molecular Beam Epitaxy. IEEE Electron Device Letters, 2017, 38, 1071-1074.	2.2	60

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145	Wide-bandgap Gallium Nitride p-channel MISFETs with enhanced performance at high temperature. , 2017, , .		2
146	S-shaped negative differential resistance in III-Nitride blue quantum-well laser diodes grown by plasma-assisted MBE. , 2017, , .		1
147	Extended Defect Propagation in Highly Tensile-Strained Ge Waveguides. Crystals, 2017, 7, 157.	1.0	5
148	Near-field Enhancement and Optimal Performance in Metamaterial Terahertz Modulators Based on 2D-materials. , 2016, , .		0
149	Atomic Layer Deposition of Al ₂ O ₃ on WSe ₂ Functionalized by Titanyl Phthalocyanine. ACS Nano, 2016, 10, 6888-6896.	7.3	69
150	Room temperature weak ferromagnetism in Sn ^{1-x} MnxSe ₂ 2D films grown by molecular beam epitaxy. APL Materials, 2016, 4, .	2.2	28
151	Terahertz amplification in RTD-gated HEMTs with a grating-gate wave coupling topology. Applied Physics Letters, 2016, 109, .	1.5	15
152	Sub-230 nm deep-UV emission from GaN quantum disks in AlN grown by a modified Stranski-Krastanov mode. Japanese Journal of Applied Physics, 2016, 55, 05FF06.	0.8	25
153	Intrinsic electron mobility limits in $\hat{1}^2$ -Ga ₂ O ₃ . Applied Physics Letters, 2016, 109, .	1.5	299
154	Physics-Inspired Neural Networks for Efficient Device Compact Modeling. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2016, 2, 44-49.	1.1	53
155	Two-dimensional heterojunction interlayer tunnel FET (Thin-TFET): From theory to applications. , 2016, , .		14
156	Comparing buffer leakage in PolarMOSH on SiC and free-standing GaN substrates. , 2016, , .		2
157	Demonstration of GaN HyperFETs with ALD VO ₂ . , 2016, , .		4
158	Controllable growth of layered selenide and telluride heterostructures and superlattices using molecular beam epitaxy. Journal of Materials Research, 2016, 31, 900-910.	1.2	85
159	Vertical Ga ₂ O ₃ Schottky barrier diodes on single-crystal $\hat{1}^2$ -Ga ₂ O ₃ (\hat{a}^201) substrates. , 2016, , .		1
160	Layered transition metal dichalcogenides: promising near-lattice-matched substrates for GaN growth. Scientific Reports, 2016, 6, 23708.	1.6	76
161	Investigation of forward transient characteristics of vertical GaN-on-GaN p-n diodes. , 2016, , .		1
162	First demonstration of strained AlN/GaN/AlN quantum well FETs on SiC. , 2016, , .		4

#	ARTICLE	IF	CITATIONS
163	Ultralow-Leakage AlGaIn/GaN High Electron Mobility Transistors on Si With Non-Alloyed Regrown Ohmic Contacts. IEEE Electron Device Letters, 2016, 37, 16-19.	2.2	37
164	1.7-kV and 0.55- $\text{m}\Omega\cdot\text{cm}^2$ GaN p-n Diodes on Bulk GaN Substrates With Avalanche Capability. IEEE Electron Device Letters, 2016, 37, 161-164.	2.2	153
165	Scanning Tunneling Microscopy and Spectroscopy of Air Exposure Effects on Molecular Beam Epitaxy Grown WSe_2 Monolayers and Bilayers. ACS Nano, 2016, 10, 4258-4267.	7.3	72
166	Exceptional Terahertz Wave Modulation in Graphene Enhanced by Frequency Selective Surfaces. ACS Photonics, 2016, 3, 315-323.	3.2	67
167	Near unity ideality factor and Shockley-Read-Hall lifetime in GaN-on-GaN p-n diodes with avalanche breakdown. Applied Physics Letters, 2015, 107, .	1.5	146
168	High breakdown single-crystal GaN p-n diodes by molecular beam epitaxy. Applied Physics Letters, 2015, 107, .	1.5	53
169	Polarization-induced Zener tunnel diodes in GaN/InGaIn/GaN heterojunctions. Applied Physics Letters, 2015, 107, .	1.5	32
170	1.9-kV AlGaIn/GaN Lateral Schottky Barrier Diodes on Silicon. IEEE Electron Device Letters, 2015, 36, 375-377.	2.2	160
171	GaN-on-GaN p-n power diodes with 3.48 kV and 0.95 $\text{mA}\cdot\text{cm}^2$: A record high figure-of-merit of 12.8 GW/cm^2 . , 2015, , .		25
172	Graphene nanoribbon field-effect transistors on wafer-scale epitaxial graphene on SiC substrates. APL Materials, 2015, 3, .	2.2	72
173	Self-assembled Ge QDs Formed by High-Temperature Annealing on Al(Ga)As (001). Journal of Electronic Materials, 2015, 44, 1338-1343.	1.0	2
174	Low temperature AlN growth by MBE and its application in HEMTs. Journal of Crystal Growth, 2015, 425, 133-137.	0.7	23
175	THz devices based on 2D electron systems. , 2015, , .		1
176	Two-Dimensional Heterojunction Interlayer Tunneling Field Effect Transistors (Thin-TFETs). IEEE Journal of the Electron Devices Society, 2015, 3, 200-207.	1.2	105
177	Comprehensive structural and optical characterization of MBE grown MoSe_2 on graphite, CaF_2 and graphene. 2D Materials, 2015, 2, 024007.	2.0	120
178	High-voltage polarization-induced vertical heterostructure p-n junction diodes on bulk GaN substrates. , 2015, , .		3
179	Dual optical marker Raman characterization of strained GaN-channels on AlN using AlN/GaN/AlN quantum wells and ^{15}N isotopes. Applied Physics Letters, 2015, 106, .	1.5	13
180	Unique opportunity to harness polarization in GaN to override the conventional power electronics figure-of-merits. , 2015, , .		7

#	ARTICLE	IF	CITATIONS
181	Lens-coupled folded-dipole antennas for terahertz detection and imaging. IET Microwaves, Antennas and Propagation, 2015, 9, 1213-1220.	0.7	11
182	Full-wave hydrodynamic model for predicting THz emission from grating-gate RTD-gated plasma wave HEMTs. , 2015, , .		3
183	Esaki Diodes in van der Waals Heterojunctions with Broken-Gap Energy Band Alignment. Nano Letters, 2015, 15, 5791-5798.	4.5	319
184	Deep-UV LEDs using polarization-induced doping: Electroluminescence at cryogenic temperatures. , 2015, , .		1
185	Impact of CF ₄ plasma treatment on threshold voltage and mobility in Al ₂ O ₃ /InAlN/GaN MOSHEMTs. Applied Physics Express, 2014, 7, 031002.	1.1	19
186	Design, fabrication and characterization of 585 GHz integrated focal-plane arrays based on heterostructure backward diodes. , 2014, , .		4
187	Approaching real-time terahertz imaging with photo-induced coded apertures and compressed sensing. Electronics Letters, 2014, 50, 801-803.	0.5	33
188	Electron transport in 2D crystal semiconductors and their device applications. , 2014, , .		2
189	Ge quantum dots encapsulated by AlAs grown by molecular beam epitaxy on GaAs without extended defects. Applied Physics Letters, 2014, 104, .	1.5	5
190	Single particle transport in two-dimensional heterojunction interlayer tunneling field effect transistor. Journal of Applied Physics, 2014, 115, .	1.1	94
191	Vertical heterojunction of MoS ₂ and WSe ₂ . , 2014, , .		4
192	Approaching real-time terahertz imaging using photo-induced reconfigurable aperture arrays. Proceedings of SPIE, 2014, , .	0.8	4
193	Chemical mechanical planarization of gold. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, 021402.	0.9	4
194	Electronic transport properties of top-gated epitaxial-graphene nanoribbon field-effect transistors on SiC wafers. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2014, 32, 012202.	0.6	4
195	Thermal Conductivity of Monolayer Molybdenum Disulfide Obtained from Temperature-Dependent Raman Spectroscopy. ACS Nano, 2014, 8, 986-993.	7.3	666
196	AlGaIn/GaN HEMTs on Si by MBE with regrown contacts and $f_{T} = 153$ GHz. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 887-889.	0.8	10
197	Faceted sidewall etching of n-GaN on sapphire by photoelectrochemical wet processing. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2014, 32, .	0.6	7
198	Two-dimensional electron gases in strained quantum wells for AlN/GaN/AlN double heterostructure field-effect transistors on AlN. Applied Physics Letters, 2014, 104, .	1.5	42

#	ARTICLE	IF	CITATIONS
199	GaN lateral PolarSJs: Polarization-doped super junctions. , 2014, , .		2
200	Tunnel-injection quantum dot deep-ultraviolet light-emitting diodes with polarization-induced doping in III-nitride heterostructures. Applied Physics Letters, 2014, 104, 021105.	1.5	77
201	High-voltage field effect transistors with wide-bandgap $\text{In}^2\text{-Ga}_2\text{O}_3$ nanomembranes. Applied Physics Letters, 2014, 104, .	1.5	288
202	Coded-Aperture Imaging Using Photo-Induced Reconfigurable Aperture Arrays for Mapping Terahertz Beams. IEEE Transactions on Terahertz Science and Technology, 2014, 4, 321-327.	2.0	47
203	GaN Heterostructure Barrier Diodes Exploiting Polarization-Induced δ -Doping. IEEE Electron Device Letters, 2014, 35, 615-617.	2.2	7
204	Atomic Structure of Thin MoSe ₂ Films Grown by Molecular Beam Epitaxy. Microscopy and Microanalysis, 2014, 20, 164-165.	0.2	19
205	Graphene nanoribbon FETs for digital electronics: experiment and modeling. International Journal of Circuit Theory and Applications, 2013, 41, 603-607.	1.3	5
206	Electrical Noise and Transport Properties of Graphene. Journal of Low Temperature Physics, 2013, 172, 202-211.	0.6	10
207	Direct Measurement of Dirac Point Energy at the Graphene/Oxide Interface. Nano Letters, 2013, 13, 131-136.	4.5	67
208	Gate-recessed integrated E/D GaN HEMT technology with $f_{T,max} > 300$ GHz. IEEE Electron Device Letters, 2013, 34, 741-743.	2.2	94
209	Polarization-Induced GaN-on-Insulator E/D Mode p-Channel Heterostructure FETs. IEEE Electron Device Letters, 2013, 34, 852-854.	2.2	55
210	Time delay analysis in high speed gate-recessed E-mode InAlN HEMTs. Solid-State Electronics, 2013, 80, 67-71.	0.8	7
211	Ultrascaled InAlN/GaN High Electron Mobility Transistors with Cutoff Frequency of 400 GHz. Japanese Journal of Applied Physics, 2013, 52, 08JN14.	0.8	66
212	Evolution of strain in aluminum gallium nitride/gallium nitride high electron mobility transistors under on-state bias. Journal of Applied Physics, 2013, 114, 064507.	1.1	3
213	InGaN Channel High-Electron-Mobility Transistors with InAlGaN Barrier and $f_{T,max}$ of 260/220 GHz. Applied Physics Express, 2013, 6, 016503.	1.1	35
214	Noise performance of RTD-gated plasma-wave HEMT THz detectors. , 2013, , .		0
215	Exfoliated MoTe ₂ field-effect transistor. , 2013, , .		3
216	A unique photoemission method to measure semiconductor heterojunction band offsets. Applied Physics Letters, 2013, 102, 012101.	1.5	11

#	ARTICLE	IF	CITATIONS
217	Exciton Dynamics in Suspended Monolayer and Few-Layer MoS ₂ 2D Crystals. ACS Nano, 2013, 7, 1072-1080.	7.3	686
218	Power Amplification at THz via Plasma Wave Excitation in RTD-Gated HEMTs. IEEE Transactions on Terahertz Science and Technology, 2013, 3, 200-206.	2.0	33
219	Comparative study of chemically synthesized and exfoliated multilayer MoS ₂ field-effect transistors. Applied Physics Letters, 2013, 102, 043116.	1.5	35
220	Quaternary Barrier InAlGaN HEMTs With f_{T}/f_{max} of 230/300 GHz. IEEE Electron Device Letters, 2013, 34, 378-380.	2.2	58
221	Graphene for Reconfigurable Terahertz Optoelectronics. Proceedings of the IEEE, 2013, 101, 1705-1716.	16.4	114
222	Tunnel-injection GaN quantum dot ultraviolet light-emitting diodes. Applied Physics Letters, 2013, 102, .	1.5	64
223	Perspectives of graphene SymFETs for THz applications. , 2013, , .		0
224	Tunnel FETs with tunneling normal to the gate. , 2013, , .		1
225	Nanomembrane GaInO high-voltage field effect transistors. , 2013, , .		1
226	Tunable Graphene-based Metamaterial Terahertz Modulators. , 2013, , .		2
227	Terahertz imaging employing graphene modulator arrays. Optics Express, 2013, 21, 2324.	1.7	113
228	Near-field enhanced graphene terahertz modulator. , 2013, , .		1
229	Dispersion-free operation in InAlN-based HEMTs with ultrathin or no passivation. , 2013, , .		7
230	Terahertz plasmonic properties of highly oriented pyrolytic graphite. Applied Physics Letters, 2013, 102, 171107.	1.5	7
231	Terahertz focal plane arrays employing heterostructure backward diodes integrated with folded dipole antennas. , 2013, , .		12
232	Graphene as transparent electrode for direct observation of hole photoemission from silicon to oxide. Applied Physics Letters, 2013, 102, .	1.5	24
233	High aspect ratio features in poly(methylglutarimide) using electron beam lithography and solvent developers. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, 06F101.	0.6	8
234	Response to "Comment on "Zener tunneling semiconducting nanotubes and graphene nanoribbon p-n junctions" [Appl. Phys. Lett. 101, 256103 (2012)]. Applied Physics Letters, 2012, 101, 256104.	1.5	0

#	ARTICLE	IF	CITATIONS
235	Fabrication of top-gated epitaxial graphene nanoribbon FETs using hydrogen-silsesquioxane. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, .	0.6	18
236	A new class of electrically tunable metamaterial terahertz modulators. Optics Express, 2012, 20, 28664.	1.7	102
237	Monolithically integrated E/D-mode InAlN HEMTs with f_{t} / $f_{\text{max}}}$ of 200/220 GHz. , 2012, , .		6
238	Ultra-thin Body GaN-on-insulator nFETs and pFETs: Towards III-nitride complementary logic. , 2012, , .		7
239	Extraordinary Control of Terahertz Beam Reflectance in Graphene Electro-absorption Modulators. Nano Letters, 2012, 12, 4518-4522.	4.5	235
240	Tunnel injection GaN/AlN quantum dot UV LED. , 2012, , .		1
241	InAlN/AlN/GaN HEMTs With Regrown Ohmic Contacts and f_{T} of 370 GHz. IEEE Electron Device Letters, 2012, 33, 988-990.	2.2	292
242	Ultra-low resistance ohmic contacts to GaN with high Si doping concentrations grown by molecular beam epitaxy. Applied Physics Letters, 2012, 101, .	1.5	42
243	First demonstration of two-dimensional WS ₂ transistors exhibiting 10 ⁵ room temperature modulation and ambipolar behavior. , 2012, , .		2
244	Polarization effects on gate leakage in InAlN/AlN/GaN high-electron-mobility transistors. Applied Physics Letters, 2012, 101, .	1.5	55
245	Perspectives of TFETs for low power analog ICs. , 2012, , .		17
246	Transistors with chemically synthesized layered semiconductor WS ₂ exhibiting 10 ⁵ room temperature modulation and ambipolar behavior. Applied Physics Letters, 2012, 101, .	1.5	237
247	Efficient terahertz electro-absorption modulation employing graphene plasmonic structures. Applied Physics Letters, 2012, 101, .	1.5	103
248	Transport properties of graphene nanoribbon transistors on chemical-vapor-deposition grown wafer-scale graphene. Applied Physics Letters, 2012, 100, .	1.5	55
249	InAs/AlGaSb heterojunction tunnel field-effect transistor with tunnelling in-line with the gate field. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 389-392.	0.8	39
250	<i>In situ</i> X-ray photoelectron spectroscopy of trimethyl aluminum and water half-cycle treatments on HF-treated and O ₃ -oxidized GaN substrates. Physica Status Solidi - Rapid Research Letters, 2012, 6, 22-24.	1.2	22
251	Determination of graphene work function and graphene-insulator-semiconductor band alignment by internal photoemission spectroscopy. Applied Physics Letters, 2012, 101, .	1.5	166
252	Broadband graphene terahertz modulators enabled by intraband transitions. Nature Communications, 2012, 3, 780.	5.8	893

#	ARTICLE	IF	CITATIONS
253	AlGaSb/InAs Tunnel Field-Effect Transistor With On-Current of 78 $\mu\text{A}/\mu\text{m}$ at 0.5 V. IEEE Electron Device Letters, 2012, 33, 363-365.	2.2	129
254	MBE-Regrown Ohmics in InAlN HEMTs With a Regrowth Interface Resistance of 0.05 Ωcm . IEEE Electron Device Letters, 2012, 33, 525-527.	2.2	118
255	Performance of AlGaSb/InAs TFETs With Gate Electric Field and Tunneling Direction Aligned. IEEE Electron Device Letters, 2012, 33, 655-657.	2.2	103
256	Ultrathin Body GaN-on-Insulator Quantum Well FETs With Regrown Ohmic Contacts. IEEE Electron Device Letters, 2012, 33, 661-663.	2.2	40
257	Effect of Optical Phonon Scattering on the Performance of GaN Transistors. IEEE Electron Device Letters, 2012, 33, 709-711.	2.2	99
258	Effect of optical phonon scattering on the performance limits of ultrafast GaN transistors. , 2011, , .		2
259	Band alignment of TFET heterojunctions and post deposition annealing effects by internal photoemission spectroscopy. , 2011, , .		0
260	Presence and origin of interface charges at atomic-layer deposited Al ₂ O ₃ /III-nitride heterojunctions. Applied Physics Letters, 2011, 99, .	1.5	140
261	Barrier height, interface charge & tunneling effective mass in ALD Al _{0.2} O ₃ /AlN/GaN HEMTs. , 2011, , .		3
262	Green luminescence of InGaN nanowires grown on silicon substrates by molecular beam epitaxy. Journal of Applied Physics, 2011, 109, .	1.1	48
263	220-GHz Quaternary Barrier InAlGaN/AlN/GaN HEMTs. IEEE Electron Device Letters, 2011, 32, 1215-1217.	2.2	71
264	Studies of Intrinsic Hot Phonon Dynamics in Suspended Graphene by Transient Absorption Microscopy. Nano Letters, 2011, 11, 3184-3189.	4.5	99
265	Unique prospects for graphene-based terahertz modulators. Applied Physics Letters, 2011, 99, .	1.5	183
266	Metal-Insulator-InAlN/AlN/GaN high electron mobility transistors with regrown ohmic contacts by molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1617-1619.	0.8	25
267	Subcritical barrier AlN/GaN E-Mode HFETs and inverters. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1620-1622.	0.8	16
268	Polarization Engineering in group III-nitride heterostructures: New opportunities for device design. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1511-1516.	0.8	83
269	N-polar III-nitride quantum well light-emitting diodes with polarization-induced doping. Applied Physics Letters, 2011, 99, .	1.5	63
270	Self-aligned InAs/Al _{0.45} Ga _{0.55} Sb vertical tunnel FETs. , 2011, , .		12

#	ARTICLE	IF	CITATIONS
271	A 570-630 GHz FREQUENCY DOMAIN TERAHERTZ SPECTROSCOPY SYSTEM BASED ON A BROADBAND QUASI-OPTICAL ZERO BIAS SCHOTTKY DIODE DETECTOR. International Journal of High Speed Electronics and Systems, 2011, 20, 629-638.	0.3	16
272	FET THZ DETECTORS OPERATING IN THE QUANTUM CAPACITANCE LIMITED REGION. International Journal of High Speed Electronics and Systems, 2011, 20, 597-609.	0.3	7
273	Performance evaluation of silicon and gallium nitride power FETs for DC/DC power converter applications. , 2010, , .		10
274	Chip-scale DC/DC power converter. , 2010, , .		1
275	Device characteristics of single-layer graphene FETs grown on copper. , 2010, , .		0
276	Polarization-mediated remote surface roughness scattering in ultrathin barrier GaN high-electron mobility transistors. Applied Physics Letters, 2010, 97, .	1.5	28
277	Polarization-engineered removal of buffer leakage for GaN transistors. Applied Physics Letters, 2010, 96, 042102.	1.5	39
278	High mobility two-dimensional electron gases in nitride heterostructures with high Al composition AlGa _N alloy barriers. Applied Physics Letters, 2010, 97, .	1.5	14
279	High-performance monolithically-integrated E/D mode InAlN/AlN/GaN HEMTs for mixed-signal applications. , 2010, , .		12
280	Threshold Voltage Control in $\text{Al}_{0.72}\text{Ga}_{0.28}\text{N}/\text{AlN}/\text{GaN}$ HEMTs by Work-Function Engineering. IEEE Electron Device Letters, 2010, 31, 954-956.	2.2	47
281	Polarization-Induced Hole Doping in Wide-Band-Gap Uniaxial Semiconductor Heterostructures. Science, 2010, 327, 60-64.	6.0	662
282	Scalability of Atomic-Thin-Body (ATB) Transistors Based on Graphene Nanoribbons. IEEE Electron Device Letters, 2010, 31, 531-533.	2.2	17
283	Gate-Recessed Enhancement-Mode InAlN/AlN/GaN HEMTs With 1.9-A/mm Drain Current Density and 800-mS/mm Transconductance. IEEE Electron Device Letters, 2010, 31, 1383-1385.	2.2	134
284	Quantum transport in graphene nanoribbons patterned by metal masks. Applied Physics Letters, 2010, 96, .	1.5	45
285	High performance E-mode InAlN/GaN HEMTs: Interface states from subthreshold slopes. , 2010, , .		1
286	Work-function engineering in novel high Al composition $\text{Al}_{0.72}\text{Ga}_{0.28}\text{N}/\text{AlN}/\text{GaN}$ HEMTs. , 2010, , .		0
287	Fabrication approach for lateral InGaAs tunnel transistors. , 2009, , .		0
288	Effect of dopant profile on current-voltage characteristics of p-n-n In _{0.53} Ga _{0.47} As tunnel junctions. , 2009, , .		0

#	ARTICLE	IF	CITATIONS
289	Ultra-scaled AlN/GaN enhancement- δ ; depletion-mode nanoribbon HEMTs. , 2009, , .		0
290	MBE-grown buffer with high breakdown voltage for nitride HEMTs on GaN template. , 2009, , .		0
291	4-NM AlN BARRIER ALL BINARY HFET WITH SiN _x GATE DIELECTRIC. International Journal of High Speed Electronics and Systems, 2009, 19, 153-159.	0.3	6
292	Field modulation in heavily-doped thin-body p δ InGaAs for tunnel FETs. , 2009, , .		0
293	Polarization-Induced Zener Tunnel Junctions in Wide-Band-Gap Heterostructures. Physical Review Letters, 2009, 103, 026801.	2.9	123
294	High field transport properties of 2D and nanoribbon graphene FETs. , 2009, , .		6
295	Operation regimes of double gated graphene nanoribbon FETs. , 2009, , .		0
296	Top-down AlN/GaN enhancement- δ ; depletion-mode nanoribbon HEMTs. , 2009, , .		13
297	Quantum transport in patterned graphene nanoribbons. , 2009, , .		1
298	4-NM AlN BARRIER ALL BINARY HFET WITH SiN _x GATE DIELECTRIC. Selected Topics in Electornics and Systems, 2009, , 153-159.	0.2	0
299	The role of setback layers on the breakdown characteristics of AlGaAs/GaAs/GaN HBTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1989-1991.	0.8	1
300	Formation of ohmic contacts to ultra-thin channel AlN/GaN HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2030-2032.	0.8	17
301	The role of doping type in setback layers on wafer-fused AlGaAs/GaAs/GaN HBTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2960-2962.	0.8	0
302	2.3 nm barrier AlN/GaN HEMTs with insulated gates. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2047-2049.	0.8	16
303	Graphene Nanoribbon Tunnel Transistors. IEEE Electron Device Letters, 2008, 29, 1344-1346.	2.2	193
304	Electrical transport properties of wafer-fused p-GaAs/n-GaN heterojunctions. Applied Physics Letters, 2008, 93, .	1.5	24
305	Photocurrent Polarization Anisotropy of Randomly Oriented Nanowire Networks. Nano Letters, 2008, 8, 1352-1357.	4.5	33
306	Zener tunneling in semiconducting nanotube and graphene nanoribbon p δ n junctions. Applied Physics Letters, 2008, 93, .	1.5	80

#	ARTICLE	IF	CITATIONS
307	Very low sheet resistance and Shubnikovâ€ˆde-Haas oscillations in two-dimensional electron gases at ultrathin binary AlNâ€ˆGaN heterojunctions. Applied Physics Letters, 2008, 92, .	1.5	40
308	AlN/GaN Insulated-Gate HEMTs With 2.3 A/mm Output Current and 480 mS/mm Transconductance. IEEE Electron Device Letters, 2008, 29, 661-664.	2.2	141
309	Polarization Induced Graded AlGaIn p-n Junction grown by MBE. , 2008, , .		0
310	DC Characteristics of AlGaAs/GaAs/GaN HBTs Formed by Direct Wafer Fusion. IEEE Electron Device Letters, 2007, 28, 8-10.	2.2	22
311	Polarization-Sensitive Nanowire Photodetectors Based on Solution-Synthesized CdSe Quantum-Wire Solids. Nano Letters, 2007, 7, 2999-3006.	4.5	108
312	Carrier statistics and quantum capacitance of graphene sheets and ribbons. Applied Physics Letters, 2007, 91, .	1.5	541
313	Electron mobility in graded AlGaIn alloys. Applied Physics Letters, 2006, 88, 042103.	1.5	39
314	Carrier transport and confinement in polarization-induced three-dimensional electron slabs: Importance of alloy scattering in AlGaIn. Applied Physics Letters, 2006, 88, 042109.	1.5	47
315	Polarization-Induced 3-Dimensional Electron Slabs in Graded AlGaIn Layers. Materials Research Society Symposia Proceedings, 2005, 892, 375.	0.1	0
316	Shaping terahertz pulses using structured metal films. , 2005, , .		1
317	TEMPERATURE DEPENDENT I-V CHARACTERISTICS OF AlGaIn/GaN HBTS AND GaN BJTS. International Journal of High Speed Electronics and Systems, 2004, 14, 819-824.	0.3	10
318	High Breakdown Voltage AlGaInâ€ˆGaN HEMTs Achieved by Multiple Field Plates. IEEE Electron Device Letters, 2004, 25, 161-163.	2.2	300
319	AlGaIn/GaN polarization-doped field-effect transistor for microwave power applications. Applied Physics Letters, 2004, 84, 1591-1593.	1.5	87
320	n-AlGaAs/p-GaAs/n-GaN heterojunction bipolar transistor wafer-fused at 550â€ˆ750â€ˆC. Applied Physics Letters, 2003, 83, 560-562.	1.5	5
321	Wafer-fused AlGaAs/GaAs/GaN heterojunction bipolar transistor. Applied Physics Letters, 2003, 82, 820-822.	1.5	11
322	Very high voltage operation (>330 V) with high current gain of AlGaIn/GaN HBTs. IEEE Electron Device Letters, 2003, 24, 141-143.	2.2	44
323	Memory Effect and Redistribution of Mg into Sequentially Regrown GaN Layer by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2003, 42, 50-53.	0.8	158
324	Realization of wide electron slabs by polarization bulk doping in graded IIIâ€ˆV nitride semiconductor alloys. Applied Physics Letters, 2002, 81, 4395-4397.	1.5	163

#	ARTICLE	IF	CITATIONS
325	The First Wafer-fused AlGaAs-GaAs-GaN Heterojunction Bipolar Transistor. Materials Research Society Symposia Proceedings, 2002, 743, L12.10.1.	0.1	1
326	Ultrashort hole capture time in Mg-doped GaN thin films. Applied Physics Letters, 2002, 81, 3975-3977.	1.5	13
327	GaN HBT: toward an RF device. IEEE Transactions on Electron Devices, 2001, 48, 543-551.	1.6	73
328	Heavy doping effects in Mg-doped GaN. Journal of Applied Physics, 2000, 87, 1832-1835.	1.1	355
329	Resonantly enhanced optical transmission through a single subwavelength aperture using nanostructured dielectrics. , 0, , .		0
330	The influence of aperture shape on the enhanced transmission properties of a periodic array of subwavelength apertures. , 0, , .		1
331	Photoelectric Generation Coefficient of Bâ€Gallium Oxide during Exposure to Highâ€Energy Ionizing Radiation. Physica Status Solidi (A) Applications and Materials Science, 0, , 2100700.	0.8	0